N-Channel 60 V (D-S) Super Junction Power MOSFET

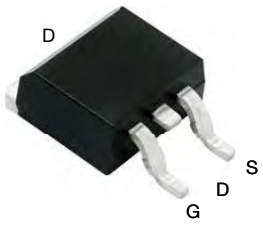
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (mΩ)(Typ.)	I_D (A)[a] (Max.)
60	1.3 at V_{GS} = 10 V	250

FEATURES

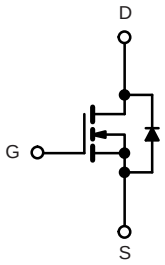
- 175 °C Junction Temperature
- DT-Trench Power MOSFET
- Material categorization:

RoHS COMPLIANT

TO-263



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (T_J = 175 °C)[b]	T_C = 25 °C	I_D	250	A
	T_C = 100 °C		198[a]	
Pulsed Drain Current		I_{DM}	1000	
Continuous Source Current (Diode Conduction)		I_S	250[a]	
Avalanche Current		I_{AS}	220	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E_{AS}	835	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	362	W
	T_A = 25 °C		8.5[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	10	15	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	0.4	0.6	

Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t ≤ 10 s.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	250			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		1.3	1.7	mΩ
		V_{GS} = 10 V, I_D = 20 A, T_J = 125 °C		1.8	2.5	
		V_{GS} = 10 V, I_D = 10 A, T_J = 175 °C		2.9	4.3	
Forward Transconductance[b]	g_{fs}	V_{DS} = 5 V, I_D = 20 A		108		S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 30 V, f = 1 MHz		11880		pF
Output Capacitance	C_{oss}			1695		
Reverse Transfer Capacitance	C_{rss}			118		
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 20 A		125	193	nC
Gate-Source Charge[c]	Q_{gs}			32		
Gate-Drain Charge[c]	Q_{gd}			10		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.6 Ω I_D = 20 A, V_{GEN} = 10 V, R_g = 2.5 Ω		21		ns
Rise Time[c]	t_r			26		
Turn-Off Delay Time[c]	$t_{d(off)}$			119		
Fall Time[c]	t_f			33		
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I_{SM}				1000	A
Diode Forward Voltage	V_{SD}	I_F = 1 A, V_{GS} = 0 V		0.7	1.0	V
Reverse Recovery Time	t_{rr}	I_F = 20 A, di/dt = 500 A/µs		35		ns
Reverse Recovery Charge	Q_{rr}	I_F = 20 A, di/dt = 500 A/µs		116		nC

Notes:

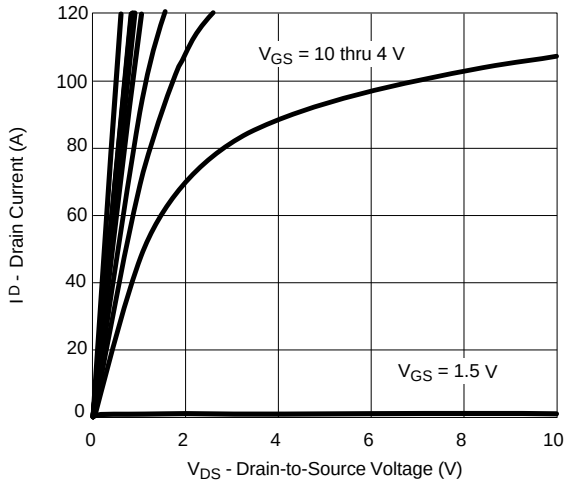
a. For design aid only; not subject to production testing.

b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

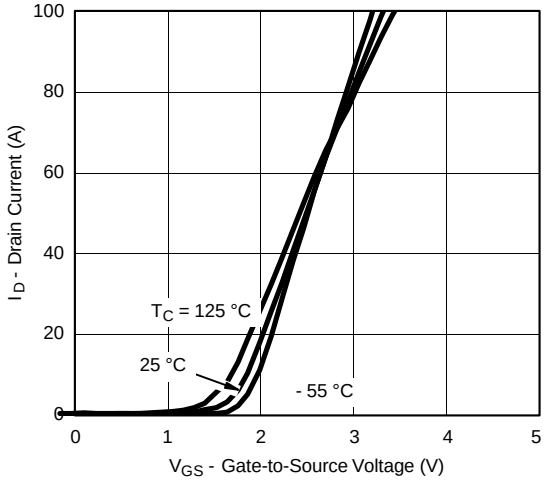
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

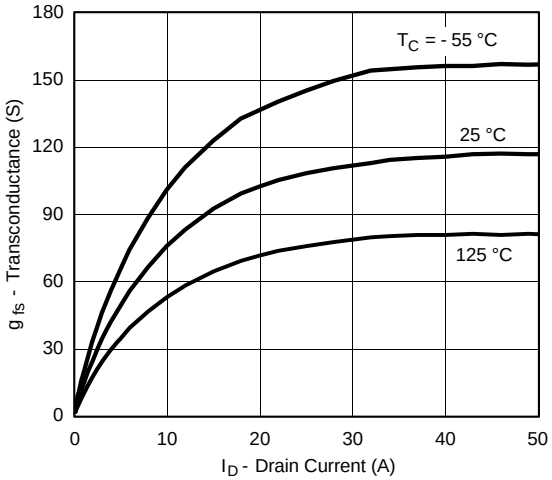
TYPICAL CHARACTERISTICS (25 °C unless noted)



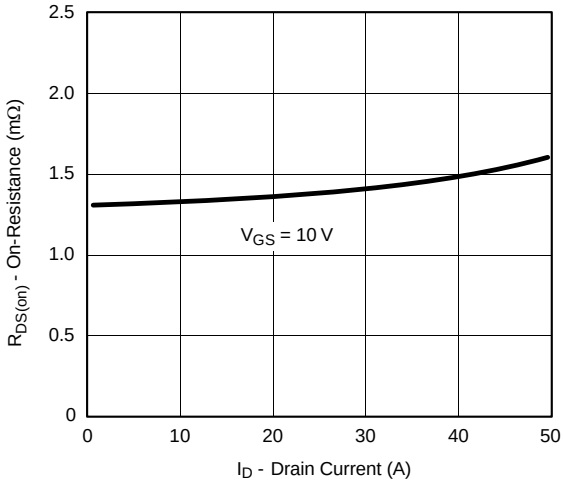
Output Characteristics



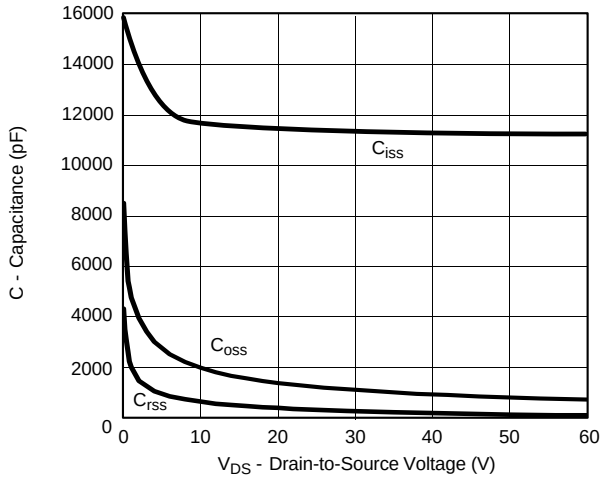
Transfer Characteristics



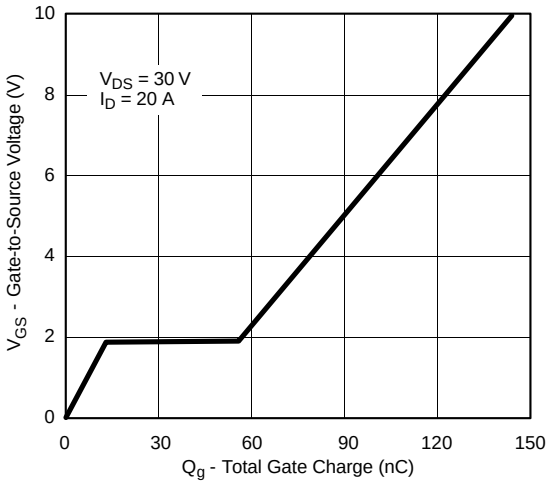
Transconductance



On-Resistance vs. Drain Current

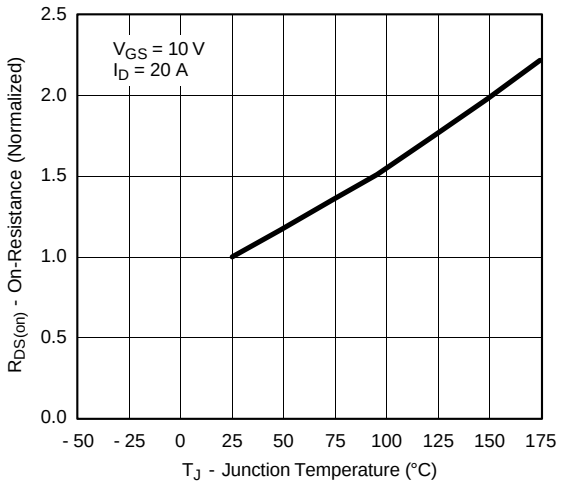


Capacitance

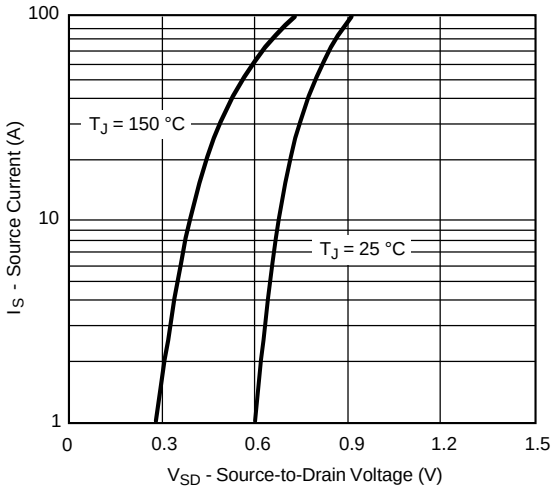


Gate Charge

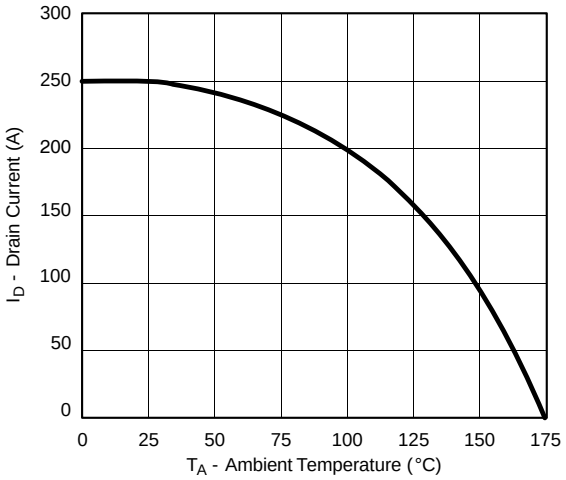
TYPICAL CHARACTERISTICS (25 °C unless noted)



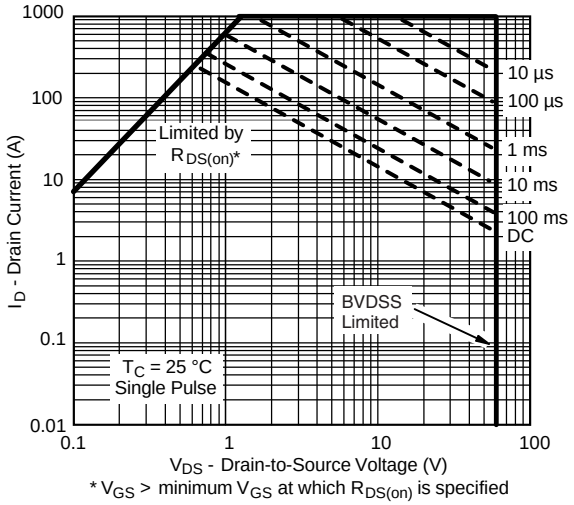
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

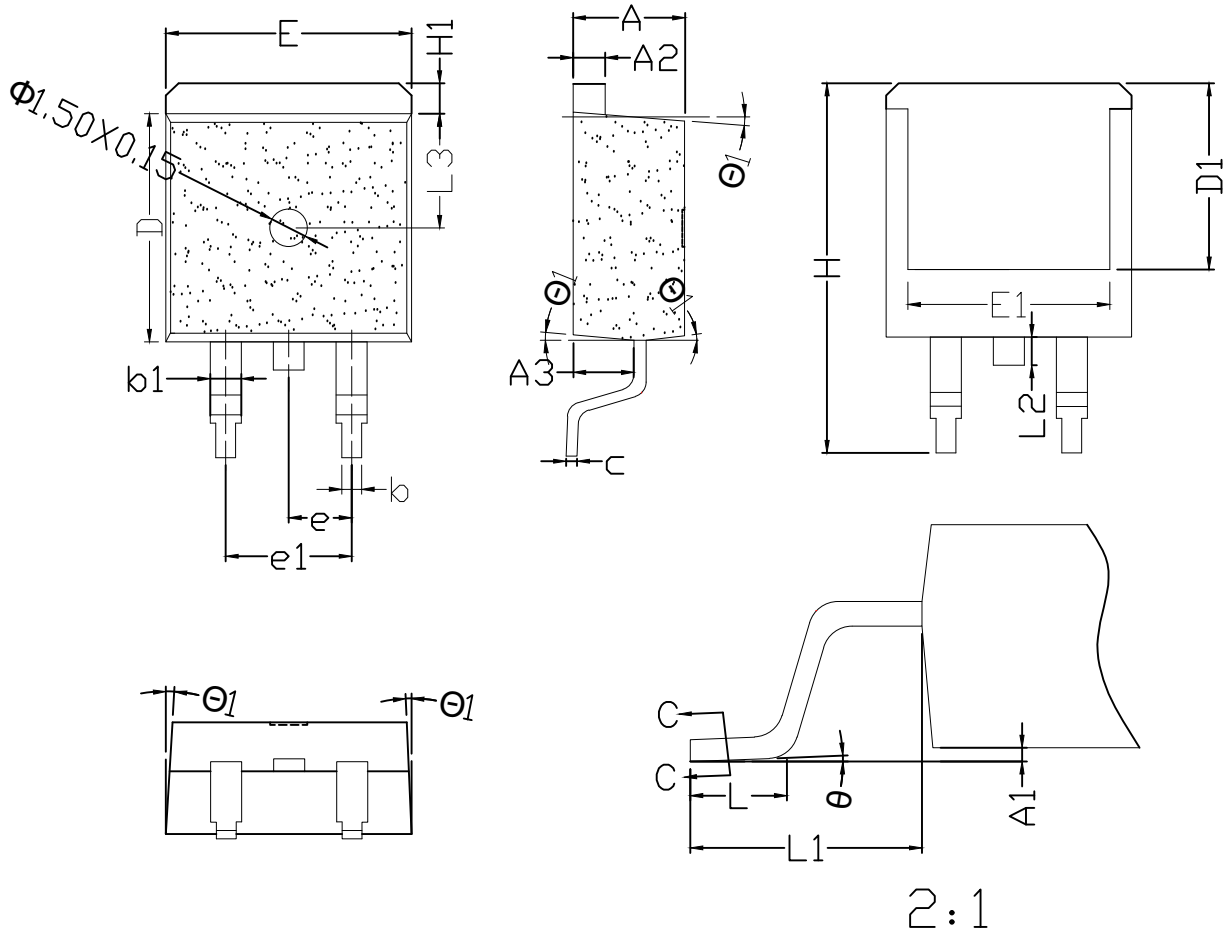


Maximum Drain Current vs. Ambient Temperature



Safe Operating Area

TO-263 PACKAGE INFORMATION



2:1

SYMBOL	mm			SYMBOL	mm		
	MIN	NOM	MAX		MIN	NOM	MAX
A	4.40	4.50	4.60	e	2.50	2.54	2.58
A1	0.00	0.10	0.20	e1		5.08REF	
A2	1.25	1.30	1.35	H	15.00	15.15	15.30
A3	2.40	2.50	2.60	H1	1.12	1.28	1.42
b	0.75	0.80	0.85	L	2.10	2.23	2.36
b1	1.25	1.33	1.42	L1	4.55	4.75	4.95
c	0.45	0.50	0.55	L2	1.10	1.30	1.50
D	9.10	9.20	9.30	L3	4.55	4.65	4.75
D1		7.50REF		θ	0°	2°	5°
E	9.88	10.02	10.15	θ1	2°	-	7°
E1	9.78	9.88	10.10				

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